

SANYO Semiconductors DATA SHEET

2SC6144

NPN Epitaxial Planar Silicon Transistor

High-Current Switching Applications

Applications

· Relay drivers, lamp drivers, motor drivers.

Features

- · Adoption of MBIT process.
- · High current capacitance.
- · Low collector-to-emitter saturation voltage.
- · High-speed switching.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		60	V
Collector-to-Emitter Voltage	VCEO		50	V
Emitter-to-Base Voltage	VEBO		5	V
Collector Current	IC		10	А
Collector Current (Pulse)	ICP		13	А
Base Current	lΒ		2	А
Collector Dissipation	P.o.		2	W
	PC	Tc=25°C	25	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

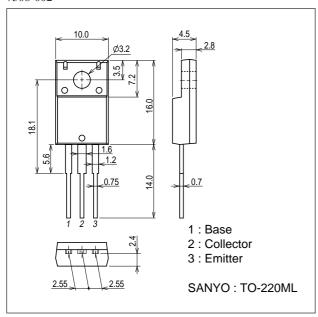
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Electrical Characteristics at Ta=25°C

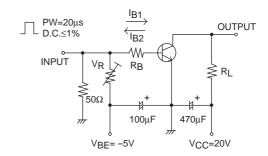
Parameter	Symbol	Conditions	Ratings			Linit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =40V, I _E =0A			10	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =4V, I _C =0A			10	μΑ
DC Current Gain	hFE	V _{CE} =2V, I _C =270mA	200		560	
Gain-Bandwidth Product	fT	VCE=10V, IC=3A		330		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		60		pF
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	IC=6A, IB=300mA		180	360	mV
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C =6A, I _B =300mA			1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=100μA, IE=0A	60			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	50			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =100μA, I _C =0A	5			V
Turn-ON Time	ton	See specified Test Circuit.		62		ns
Storage Time	t _{stg}	See specified Test Circuit.		350		ns
Fall Time	tf	See specified Test Circuit.		25		ns

Package Dimensions

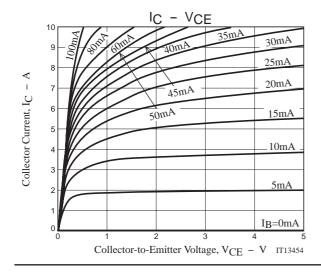
unit : mm (typ) 7508-002

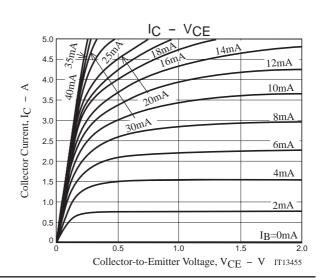


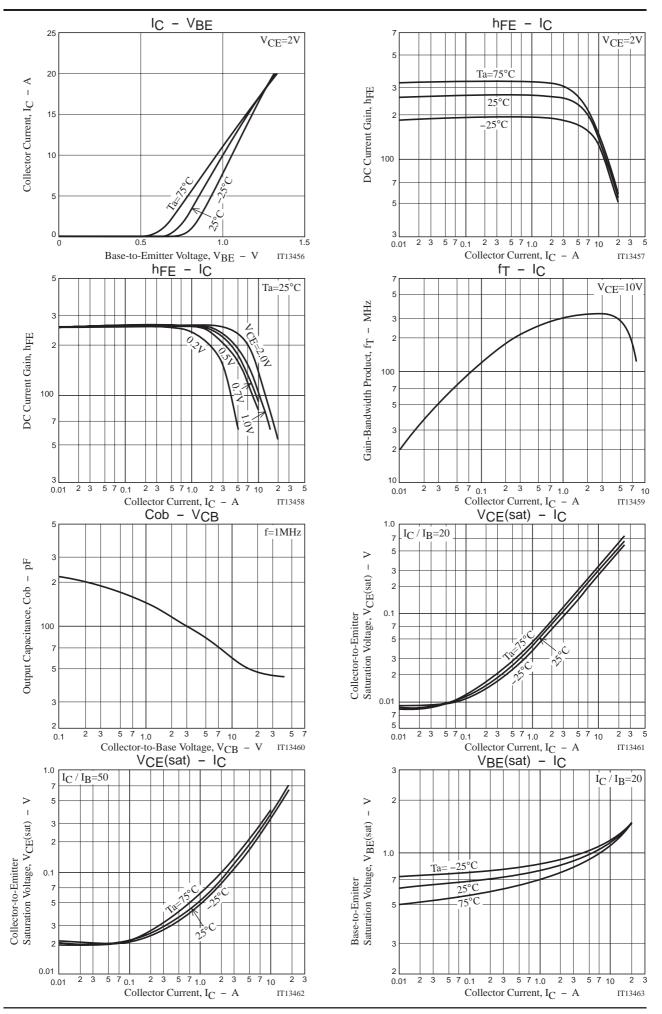
Switching Time Test Circuit

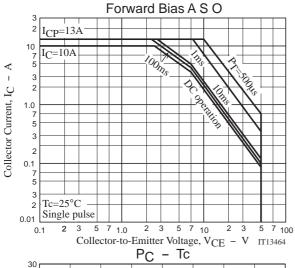


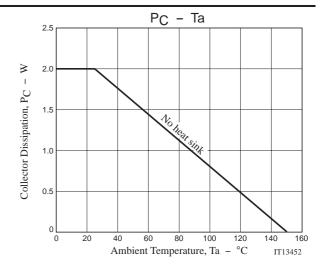
$$I_{C}=20I_{B1}=-20I_{B2}=5A$$

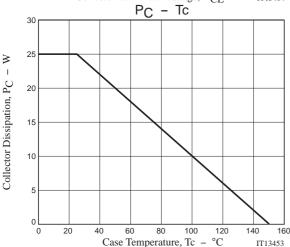












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